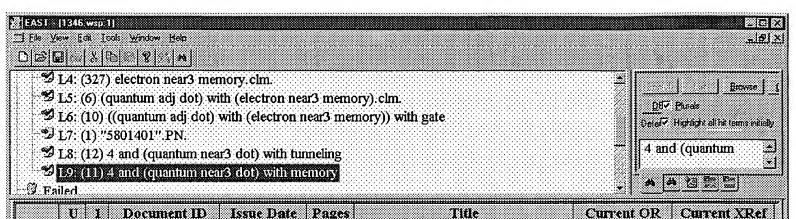


	U 1	Document ID	Issue Date	Pages	Title	Current OR	Current XRel
		US 20040076032	20040422	18	Single electron memory device	365/145	
		A1			comprising quantum dots between ga		
		US 20030197168	20031023	12		257/10	}
		A1			layer		
	гг	US 20030153151	20030814	12	Memory device with quantum dot	438/257	257/316;
		A1			and method for manufacturing the sa		257/E21.209;
	гг	US 20030054624	20030320	12	Quantum dot of single electron	438/590	257/24;
		Δ1			memory device and method for fabric		257/E21.345;
		US 20020167002	20021114	18	Single electron memory device	257/20	257/E21.209;
	1456	::Al			comprising quantum dots between ga		257/E29.301
	j j	US 20020031649	20020314	12	Quantum dot of single electron	428/209	257/E21.345;
		A1			memory device and method for fabric		257/E29.301
		. US 6670670 B2	20031230	16	Single electron memory device	257/316	257/321;
					comprising quantum dots between ga		257/325:
	- -	US 6649966 B2	20031118	11	Quantum dot of single electron	257/314	257/315;
					memory device and method for fabric		257/316;
		US 6597036 B1	20030722	11	Multi-value single electron memory	257/316	257/315;
	1.				using double-quantum dot and drivin		257/317;
)	-	US 6524883 B2	20030225	12	Quantum dot of single electron	438/94	257/E21.345;
					memory device and method for fabric		257/E29.301;
		US 6323504 B1	20011127	15	Single-electron memory device using	257/14	257/20;
					an electron-hole coulomb blockade		257/23;
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	-	US 20040076032	20040422	18	Single electron memory device	365/145	
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	,	US 20030153151	20030814			438/257	257/316;
					and method for manufacturing the sa		257/E21.209;
	-	US 20030054624	20030320	12		438/590	257/24;
		A1					257/E21.345;
		US 20020167002	20021114	18	Single electron memory device	257/20	257/E21.209;
		Aleccentric			comprising quantum dots between ga		257/E29.301
_	-	US 20020031649	20020314	12	Quantum dot of single electron	428/209	257/E21.345;
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		US 6670670 B2	20031230	16	Single electron memory device	257/316	257/321;
	1.7				comprising quantum dots between ga		257/325;
	_	US 6649966 B2	20031118	11			257/315;
	1				memory device and method for fabric		257/316;
<u></u>		US 6597036 B1	20030722	11	Multi-value single electron memory	257/316	257/315;
					using double-quantum dot and drivin		257/317;
-		US 6524883 B2	20030225	12	Quantum dot of single electron	438/94	257/E21.345;
	1				memory device and method for fabric		257/E29.301;
		US 6323504 B1	20011127	15		257/14	257/20;
					an electron-hole coulomb blockade		257/23;
-	-	US 5663571 A	19970902	50	Quantum memory	257/17	257/21;
	1					a ang pinggang ng mga panggang ng pang	257/22;
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